

## P-channel -30 V, 11 mΩ typ., -45 A STripFET™ H6 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

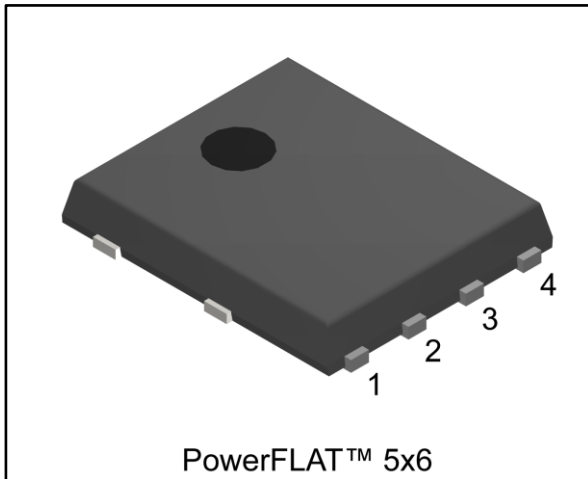
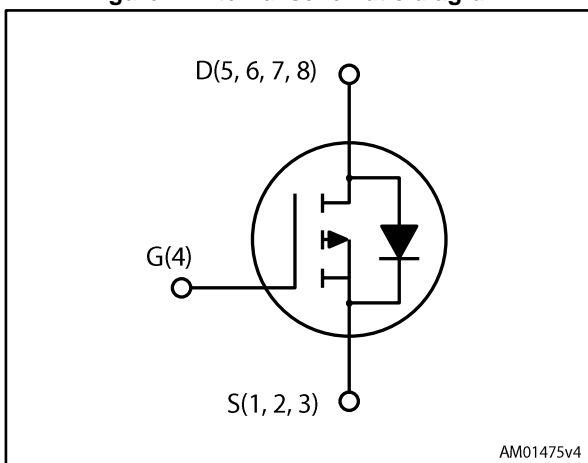


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STL45P3LLH6	-30 V	13 mΩ	-45 A

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

### Applications

- Switching applications

### Description

This device is a P-channel Power MOSFET developed using the STripFET™ H6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R<sub>DS(on)</sub> in all packages.

Table 1: Device summary

Order code	Marking	Package	Packing
STL45P3LLH6	45P3LLH6	PowerFLAT™ 5x6	Tape and reel

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# 1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	-30	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	-45	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	-34	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	-12	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	-8.7	A
$I_{DM}^{(1)(3)}$	Drain current (pulsed)	-180	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	-48	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	75	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.8	W
$T_{stg}$	Storage temperature range	- 55 to 175	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

**Notes:**

- (1) The value is rated according to  $R_{thj-c}$ .  
 (2) This value is rated according to  $R_{thj-pcb}$ .  
 (3) Pulse width is limited by safe operating area

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.00	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	$^\circ\text{C/W}$

**Notes:**

- (1) When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ sec}$

## 2 Electrical characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified)

**Table 4: On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = -1\text{ mA}$	-30			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = -30\text{ V}$			-1	$\mu\text{A}$
		$V_{GS} = 0, V_{DS} = -30\text{ V}, T_C = 125\text{ }^\circ\text{C}$ <sup>(1)</sup>			-10	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1			V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = -10\text{ V}, I_D = -6\text{ A}$		11	13	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -6\text{ A}$		16	19.5	$\text{m}\Omega$

**Notes:**

<sup>(1)</sup> Defined by design, not subject to production test.

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = -25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	2615	-	pF
$C_{oss}$	Output capacitance		-	340	-	pF
$C_{rss}$	Reverse transfer capacitance		-	235	-	pF
$Q_g$	Total gate charge	$V_{DD} = -15\text{ V}, I_D = -12\text{ A}, V_{GS} = -4.5\text{ V}$	-	24	-	nC
$Q_{gs}$	Gate-source charge		-	9	-	nC
$Q_{gd}$	Gate-drain charge		-	8	-	nC

**Table 6: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = -15\text{ V}, I_D = -6\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = -10\text{ V}$	-	13.2	-	ns
$t_r$	Rise time		-	93	-	ns
$t_{d(off)}$	Turn-off delay time		-	50	-	ns
$t_f$	Fall time		-	18	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = -6 \text{ A}$ , $V_{GS} = 0$	-		-1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = -6 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = -16 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$	-	20		ns
$Q_{rr}$	Reverse recovery charge		-	16		nC
$I_{RRM}$	Reverse recovery current		-	-1.6		A

**Notes:**

<sup>(1)</sup>Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.2 Electrical characteristics (curves)



Note: For the P-channel Power MOSFET, current and voltage polarities are reversed.

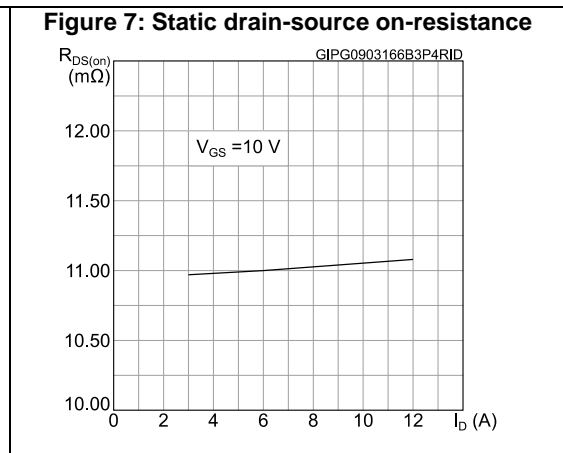
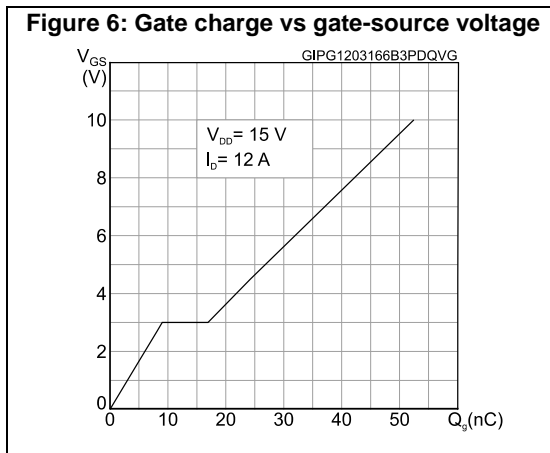
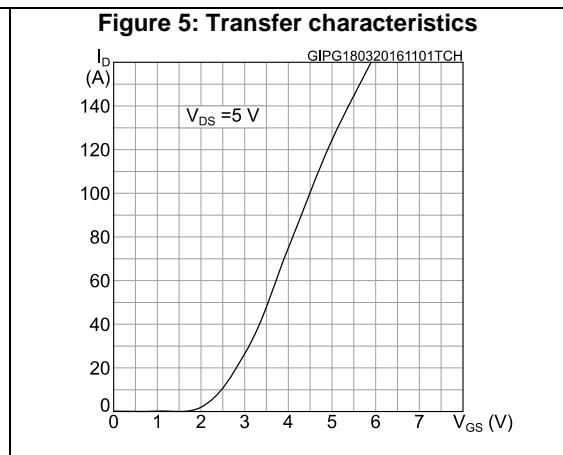
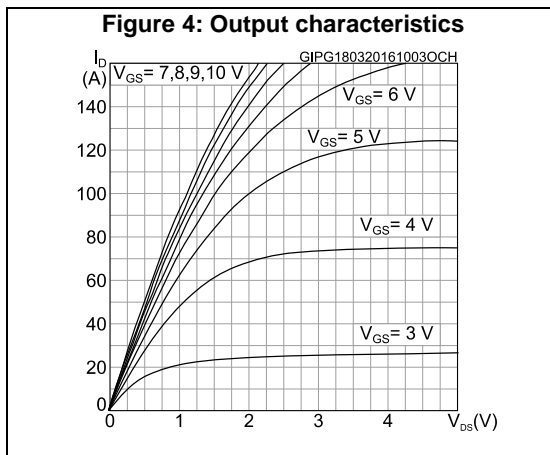
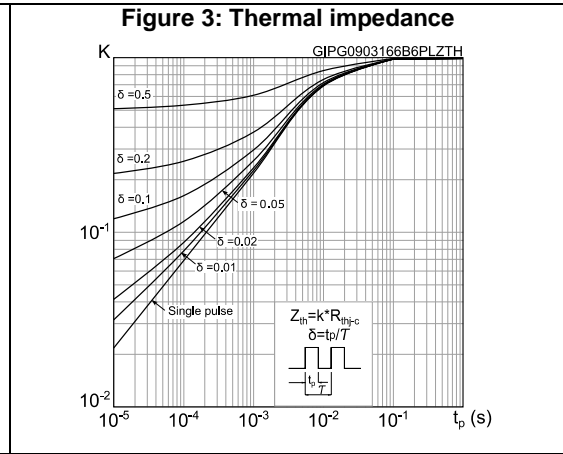
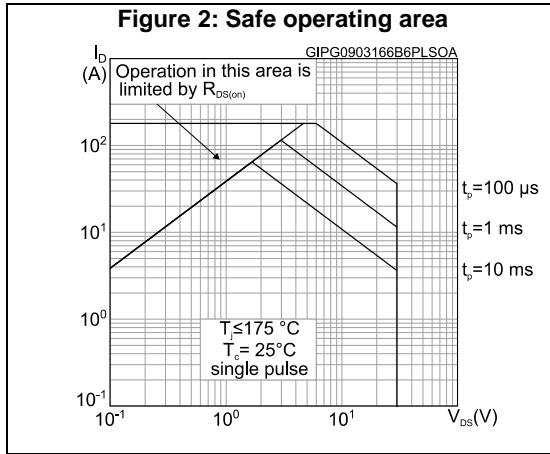


Figure 8: Capacitance variations

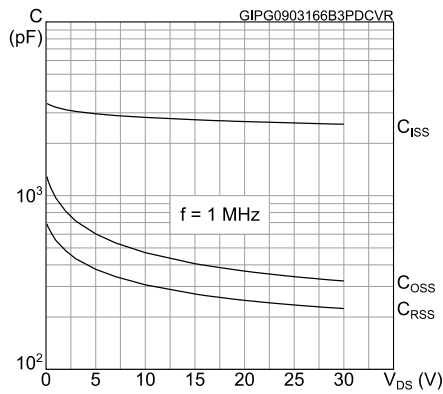


Figure 9: Normalized gate threshold voltage vs temperature

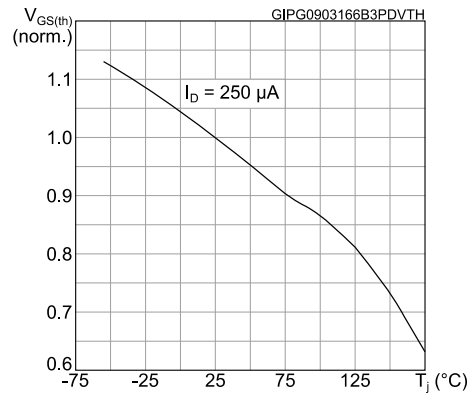


Figure 10: Normalized on-resistance vs temperature

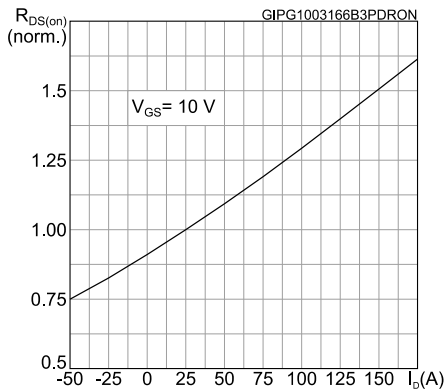


Figure 11: Normalized  $V_{(BR)DSS}$  vs temperature

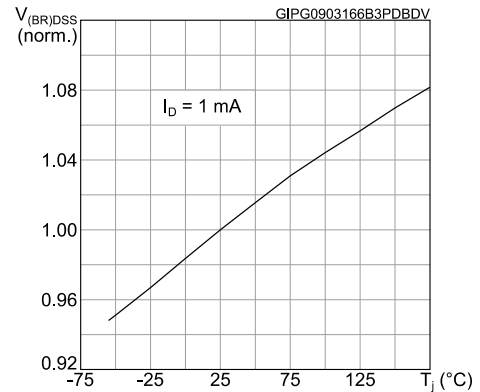
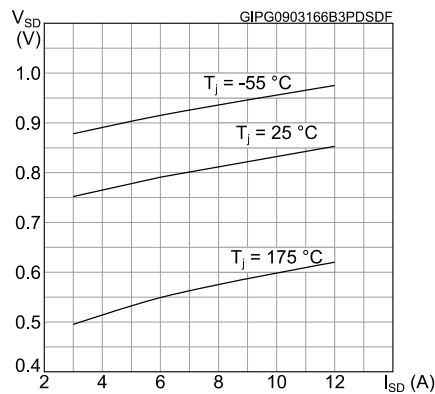


Figure 12: Source-drain diode forward characteristics



### 3 Test circuits

Figure 13: Switching times test circuit for resistive load

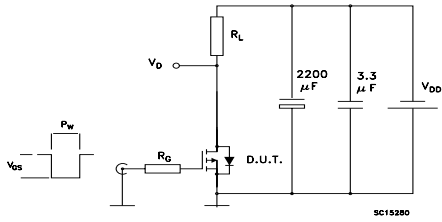


Figure 14: Gate charge test circuit

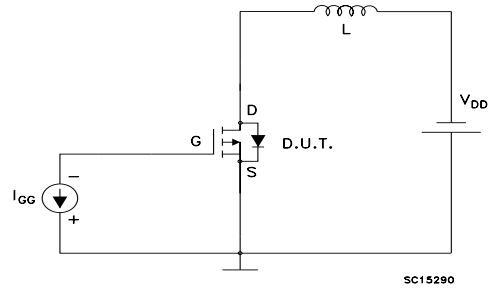
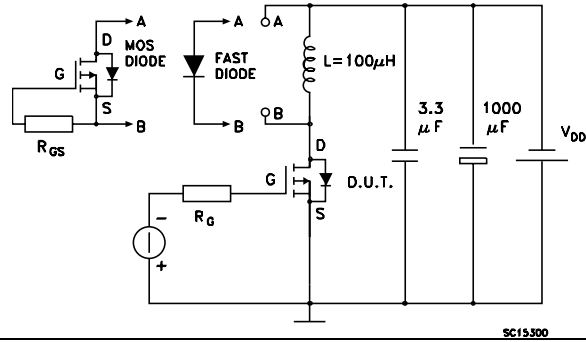


Figure 15: Test circuit for inductive load switching and diode recovery times



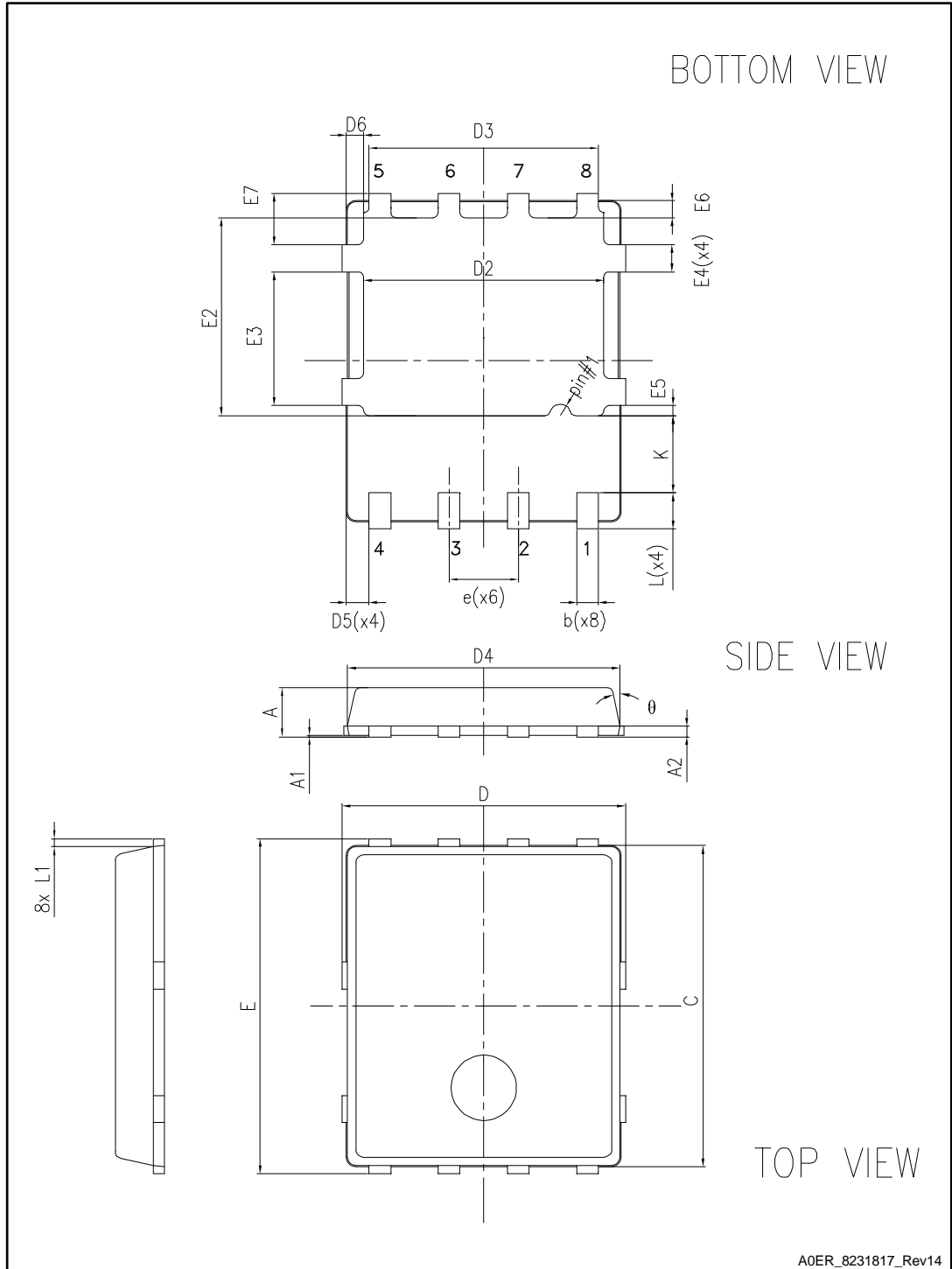


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 PowerFLAT™ 5x6 package information

Figure 16: PowerFLAT™ 5x6 type R package outline

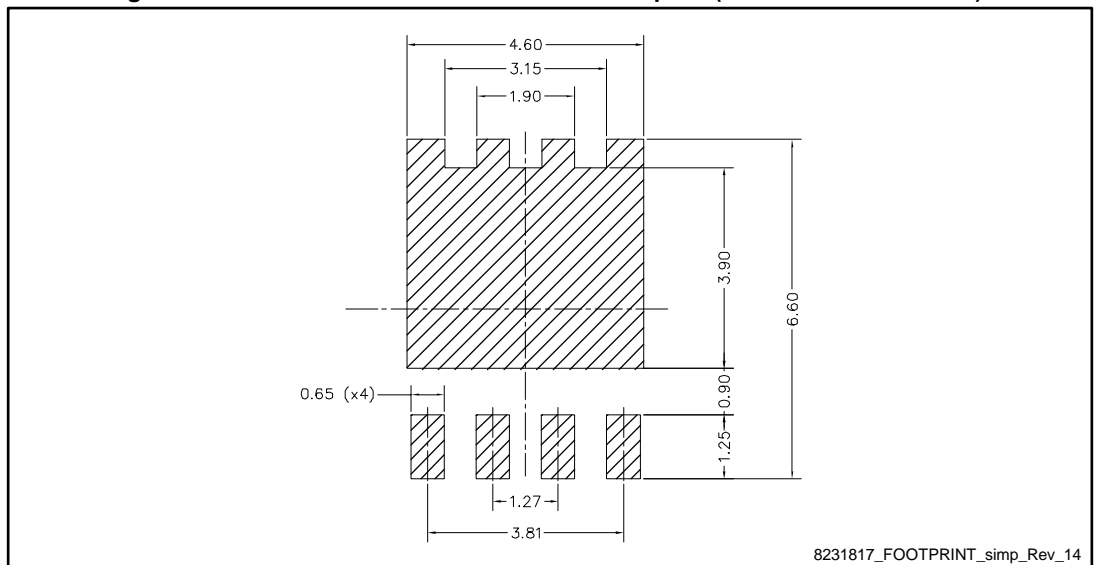


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Table 8: PowerFLAT™ 5x6 type R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.20
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	5.95	6.15	6.35
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.75	0.90	1.05
K	1.275		1.575
L	0.60		0.80
L1	0.05	0.15	0.25
θ		0°	12°

Figure 17: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



### 4.2 PowerFLAT™ 5x6 packaging information

Figure 18: PowerFLAT™ 5x6 tape (dimensions are in mm)

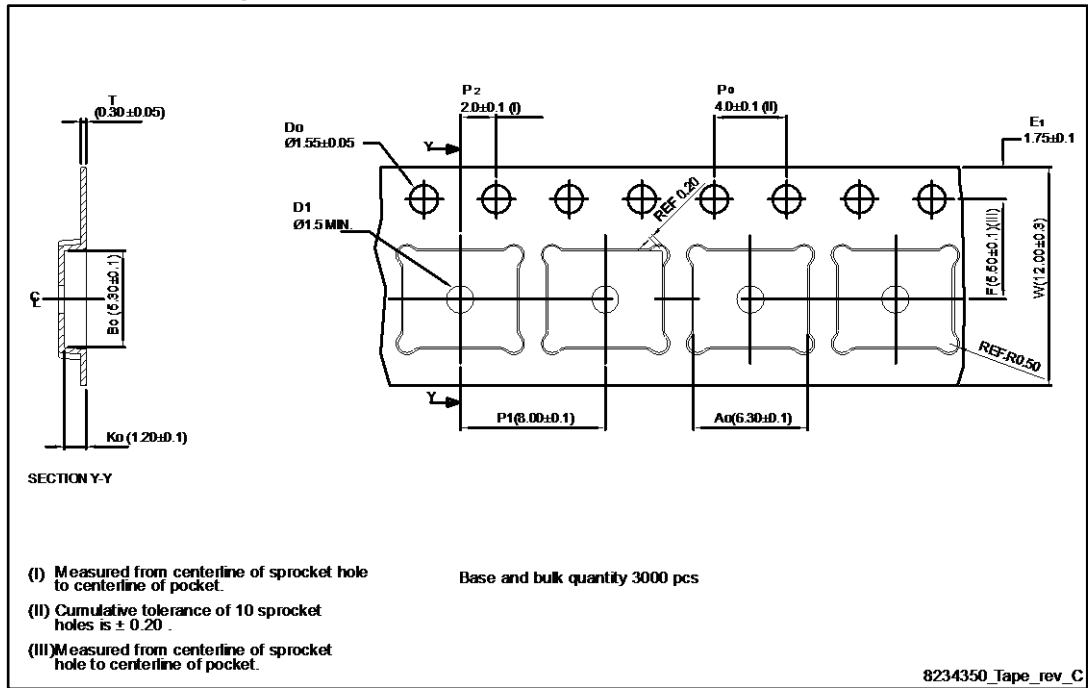


Figure 19: PowerFLAT™ 5x6 package orientation in carrier tape

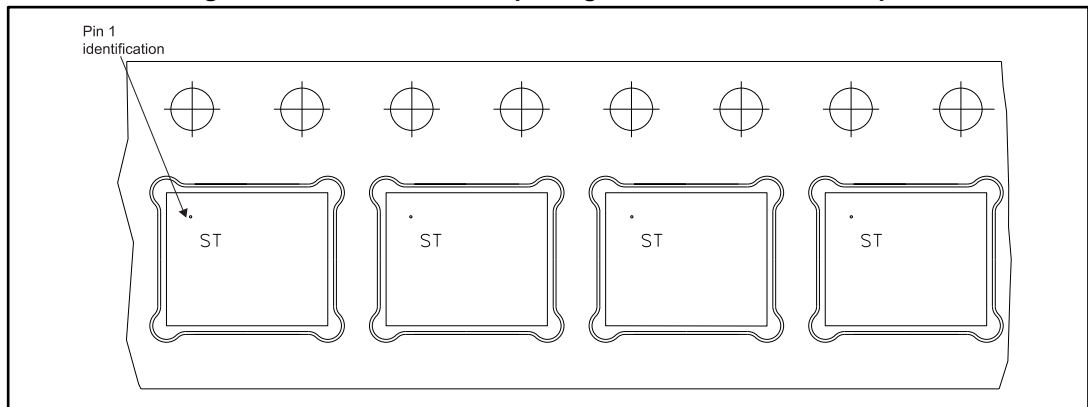
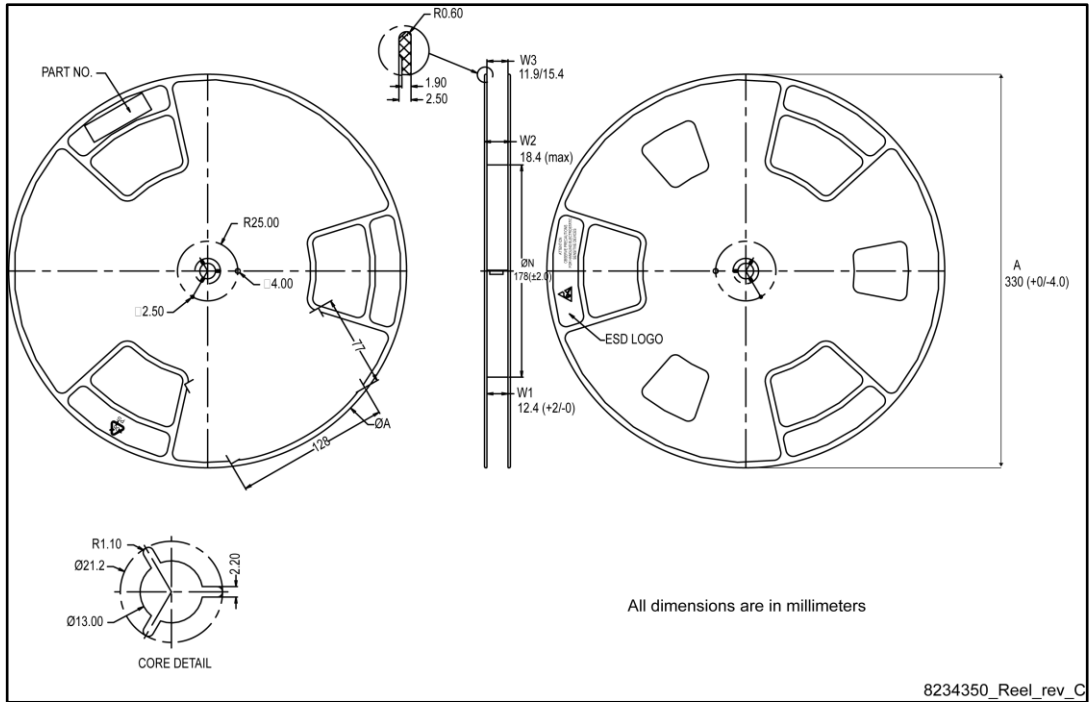


Figure 20: PowerFLAT™ 5x6 reel



## 5 Revision history

Table 9: Document revision history

Date	Revision	Changes
01-Apr-2016	1	First release.

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